USB PD power adapter SR controller

General description

EZ-PD™ PAG1S is an integrated synchronous rectifier (SR) controller and charging port controller. EZ-PD™ PAG1S is designed to fit into a traditional primary-controlled flyback system with secondary-side sensing and regulation. EZ-PD™ PAG1S is targeted towards power adapters, it fits well into high-efficiency AC-DC flyback designs for USB Power Delivery, Qualcomm Quick Charge, and other standard charging protocols. EZ-PD™ PAG1S also supports USB Power Delivery (USB PD) programmable power supply (PPS) mode.

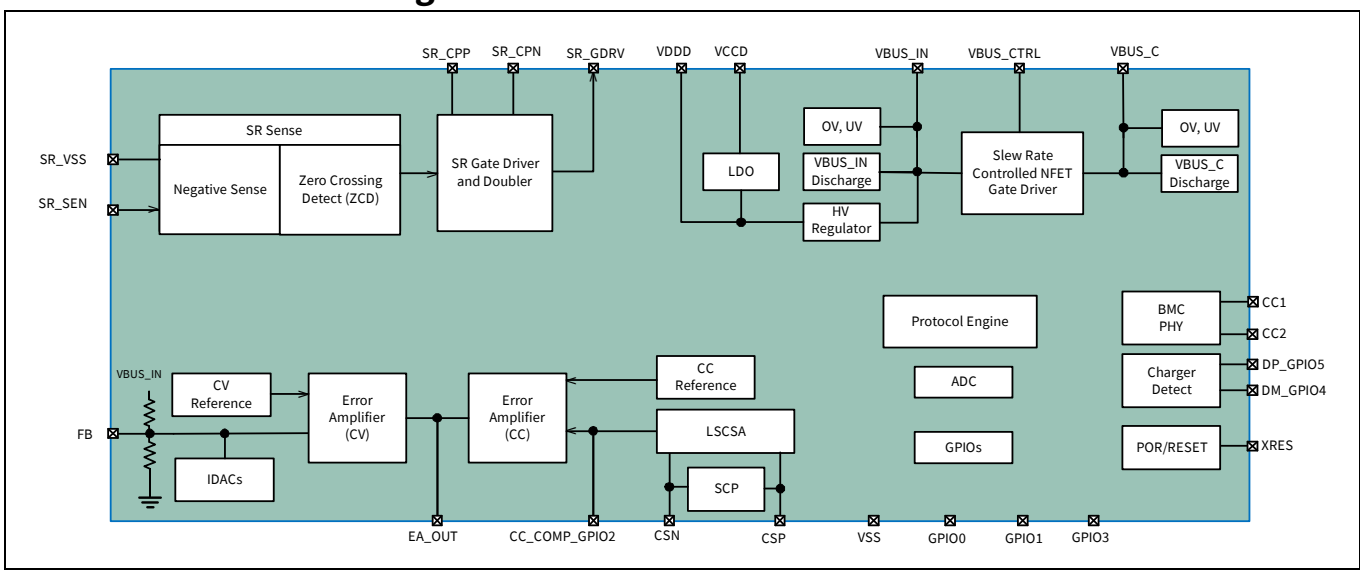
Applications

- USB PD 3.0 PPS power adapter
- Quick Charge 4.0 power adapter
- Power adapters supporting both USB PD and legacy charging

Features

- Integrates secondary-side regulation, synchronous rectifier (SR), and charging port controller
- Optimized efficiency across line and load range
- Supports both critical conduction mode (CrCM) and valley switching mode
- Switching frequency range of 20 kHz to 150 kHz
- Supports constant voltage (CV) and constant current (CC) modes of operation.
- Configurable overvoltage protection (OVP), undervoltage protection (UVP), overcurrent protection (OCP), short circuit protection (SCP), and over-temperature protection (OTP)
- Supports USB PD2.0, PD 3.0 with PPS, QC4+, QC 4.0, QC 3.0, QC 2.0, Samsung AFC, Apple charging, and BC v1.2 charging protocols
- Integrates low-side current sense amplifier (LSCSA), 2x VBUS discharge FETs, and a NFET gate driver to drive the load switch
- Protects against accidental VBUS to CC short; ESD protection on CC, VBUS, and DP/DM lines
- 24-QFN package with –40°C to +105°C extended industrial temperature range

Functional block diagram



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1 Pinout

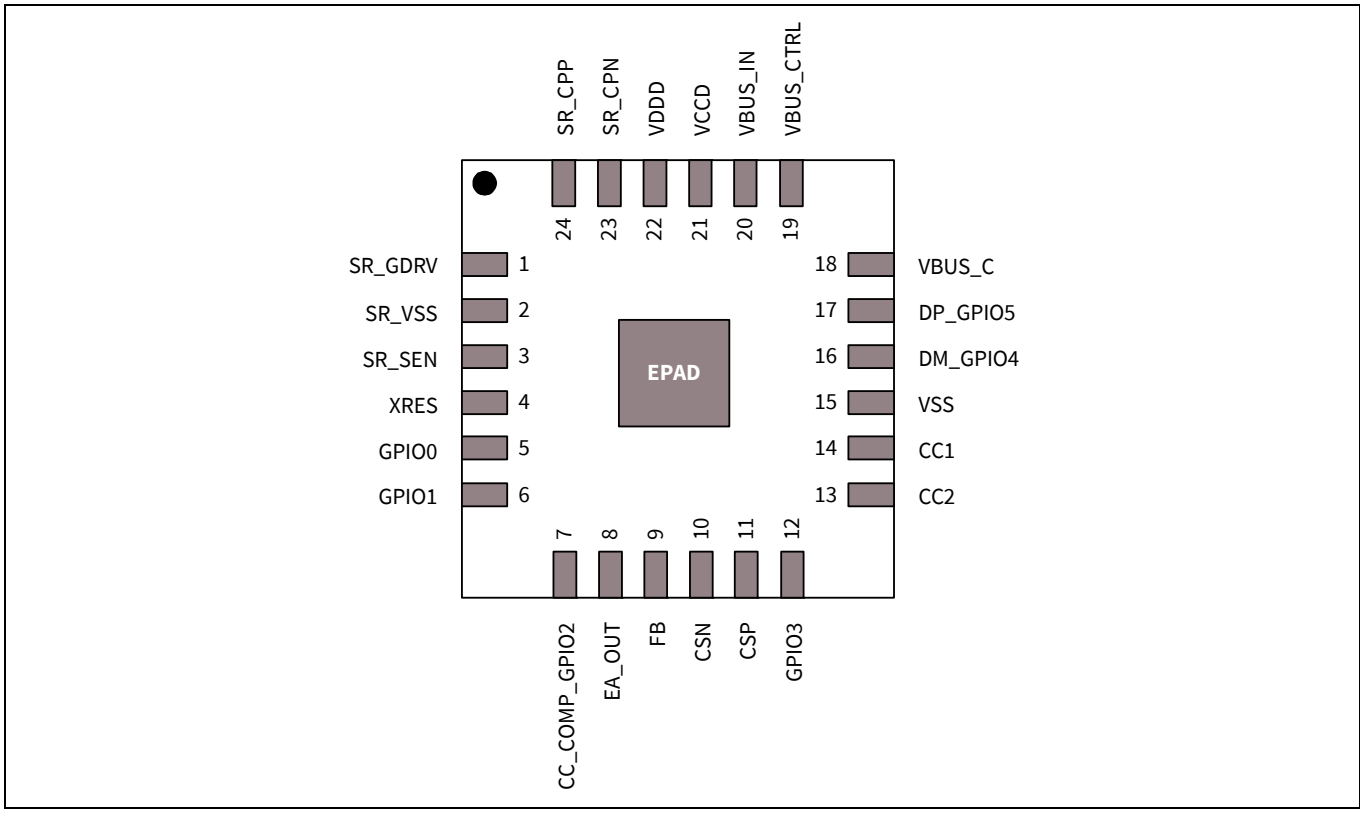


Figure 1 24-pin QFN pin map

Pinout

Table 1 EZ-PD™ PAG1S pin description

Pin number	Pin name	Description
1	SR_GDRV	Synchronous-rectifier NFET gate driver
2	SR_VSS	Synchronous-rectifier NFET ground terminal
3	SR_SEN	Synchronous-rectifier NFET drain terminal
4	XRES	External reset input
5	GPIO0	GPIO P0.0
6	GPIO1	GPIO P0.1
7	CC_COMP_GPIO2	Pin for constant current mode compensation capacitor/GPIO P0.2
8	EA_OUT	Error amplifier output
9	FB	Error amplifier feedback
10	CSN	Low-side current sense amplifier negative input
11	CSP	Low-side current sense amplifier positive input
12	GPIO3	GPIO P0.3
13	CC2	Power Delivery communication channel 2
14	CC1	Power Delivery communication channel 1
15	VSS	Ground
16	DM_GPIO4	USB D-/SWD_DATA/GPIO P0.4
17	DP_GPIO5	USB D+/SWD_CLK/GPIO P0.5
18	VBUS_C	USB Type-C VBUS monitor input
19	VBUS_CTRL	Load switch NFET gate control
20	VBUS_IN	Power source input
21	VCCD	1.8-V core voltage LDO output
22	VDDD	3.0 V–5.5 V internal LDO Output
23	SR_CPN	SR doubler capacitor negative pin
24	SR_CPP	SR doubler capacitor positive pin
25	EPAD	EPAD for ground

1.1 Pin description

SR_GDRV, SR_VSS, SR_SEN, SR_CPP, SR_CPN.

EZ-PD™ PAG1S senses the voltage across the SR NFET and appropriately controls the gate driver to achieve optimum efficiency. The gate driver (SR_GDRV) can be driven to internal VDDD or twice of VDDD to achieve better RDS-On of the external NFET. The Gate Driver can be driven to twice of VDDD using an internal doubler circuit, with the doubler capacitor connected across SR_CPP and SR_CPN pins. The source terminal of the SR FET shall be connected to SR_VSS pin.

EZ-PD™ PAG1S supports SR in QR/CrCM and valley switching. The SR sense block supports negative sense detect and Zero Crossing Detect (ZCD). The voltage at the drain node of the external NFET is sensed using a resistive divider. The internal resistor is 2 kΩ, the external resistor needs to be chosen such that the voltage at the SR_SEN pin does not exceed 21.5 V.

The external resistance on SR_SEN pin depends on turns ratio of power transformer. **Table 2** provides the values required for various values of turns ratio.

Table 2 External resistance on SR_SEN vs turns ratio

Primary : Secondary turns ratio	Rext (Ω)
4:1	10K
5:1	9K
6:1	8K
7:1	7K
8:1	6K
9:1	5K
10:1	4K

The fast-negative sense comparator can detect a minimum negative voltage of 100 mV to –200 mV on SR_SEN pin. Similarly, ZCD can detect a minimum threshold of –16 mV to 0 mV on the SR_SEN pin. See **Figure 2** and **Figure 3** for the waveforms representing the SR_GDRV functionality in CrCM and valley switching mode.

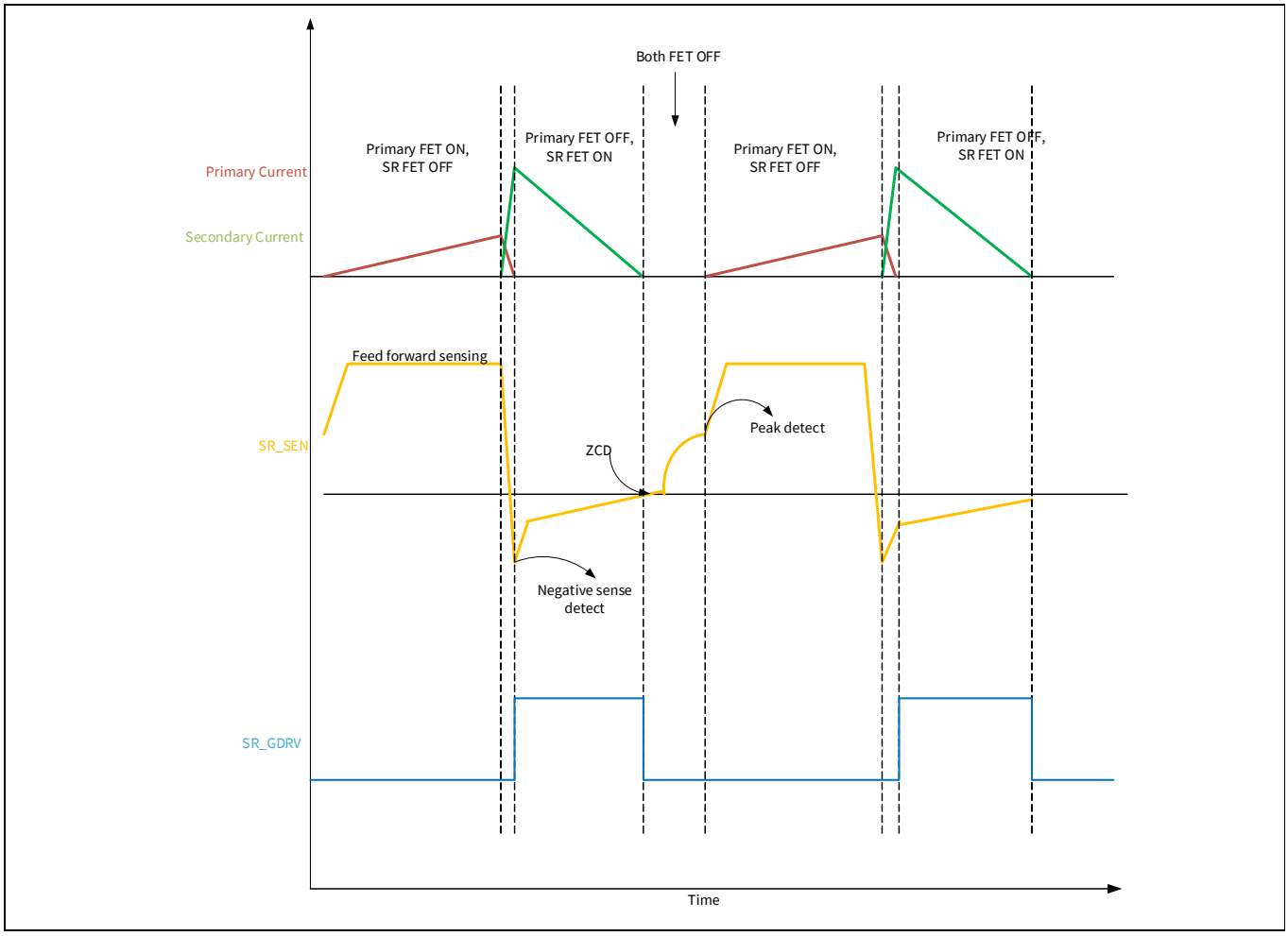


Figure 2 SR_SEN and SR_GDRV in QR/CrCM mode

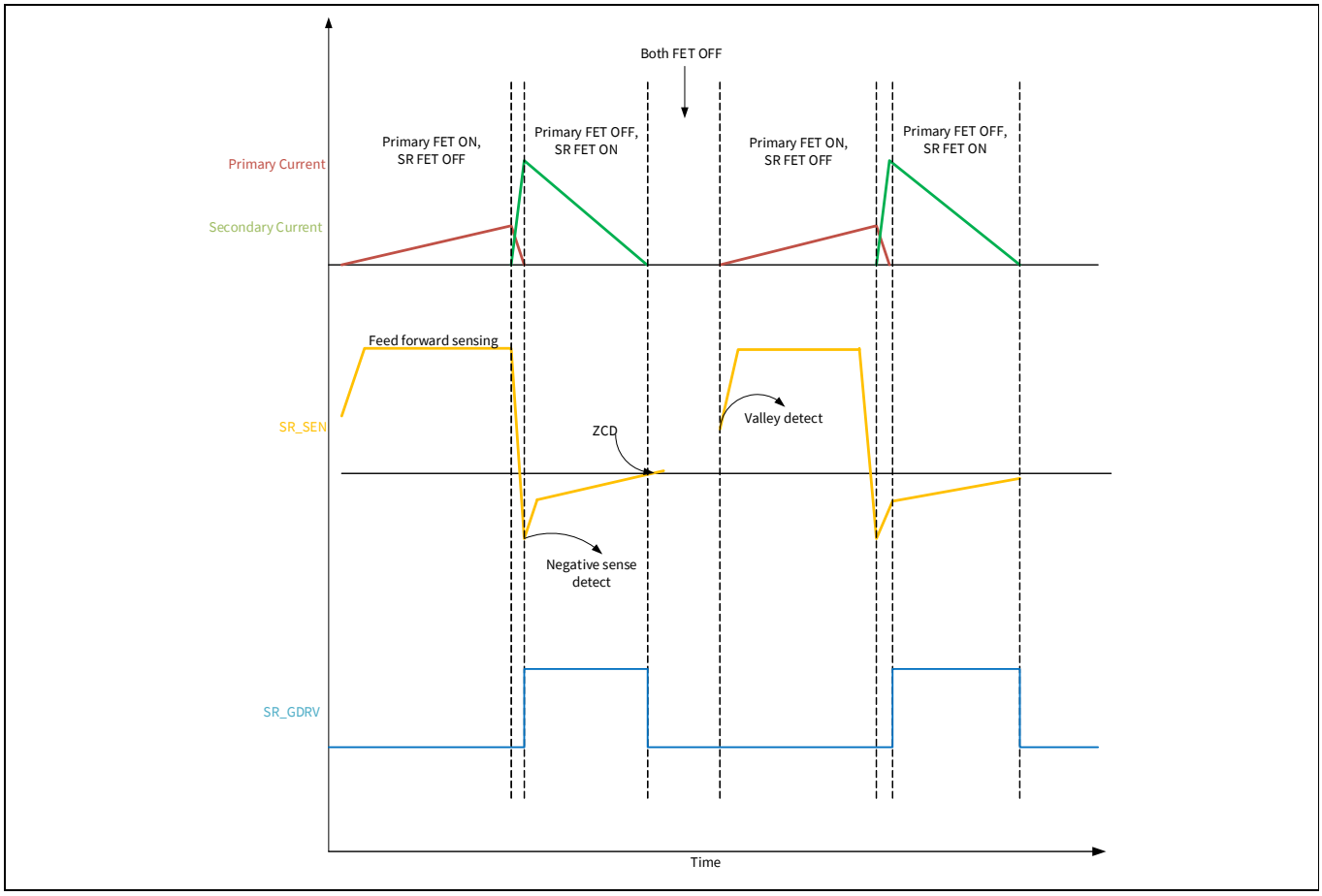


Figure 3 SR_SEN and SR_GDRV in valley switching mode

1.1.1 FB, EA_OUT, CC_COMP_GPIO2

EZ-PD™ PAG1S integrates two error amplifier blocks which handles secondary output sensing and regulation for CV and CC modes. This block is responsible for both constant voltage and constant current operations. The output of the error amplifier is routed to the EA_OUT pin. EA_OUT can further drive an opto-isolator to provide feedback to the primary controller. The negative input of the error amplifier is the feedback (FB) pin and the positive input is internal reference of 0.744 V. The FB pin has internal resistor divider of 200 kΩ and 35 kΩ, this divider sets a default voltage of 0.744 V at FB pin when VBUS_IN is at 5V. Based on the desired VBUS_C output, the voltage at the FB pin will be varied using internal current source/sink IDACs. An external compensation network is required between FB pin and EA_OUT pin, as shown in **Figure 4**.

Constant current operation makes use of an internal LSCSA, the output of which feeds into an independent error amplifier as shown in **Figure 4**. EZ-PD™ PAG1S error amplifier can ensure constant voltage regulation over 3.3 V to 21.5 V range and constant current regulation over 1 A to 3 A as required by the USB PD PPS specification.

1.1.2 CC1, CC2

CC1 and CC2 are the communication channels for USB PD protocol. EZ-PD™ PAG1S integrates a USB PD transceiver consisting of a transmitter and receiver that communicate biphase mark code (BMC) encoded data over the configuration channel (CC) channels as per the USB PD standard. All communication is half-duplex. The physical layer implements collision avoidance to minimize communication errors on the channel. This block includes all termination resistors (Rp) and their switches as required by the USB PD specification. An external 390-pF capacitor is required on both the CC1 and CC2 pins.

1.1.3 DP_GPIO4, DM_GPIO5

The DP and DM lines are the standard USB D+ and D– lines. EZ-PD™ PAG1S integrates a charge detect block, which handles legacy charging protocols such as BC 1.2, Quick Charge, Apple charging, and Samsung AFC. This block integrates all the terminations required for these charging protocols and no external components are required. When legacy charging is not required in the system, the same DP and DM lines can be reused as standard GPIOs.

1.1.4 VBUS_IN, VDDD, VCCD

EZ-PD™ PAG1S integrates a high-voltage regulator, which is powered from the VBUS_IN rail, the output of the regulator powers the VDDD rail. The input to the regulator can range from 3.3 V minimum to 21.5 V maximum. When the input is between 5.5 V to 21.5 V, the typical output of the regulator is 5 V. For inputs from 3.3 V to 5.5 V, the regulator output is VBUS_IN – 300 mV.

The regulator can drive a maximum load current of 50 mA, which includes the chip current consumption. This regulator is not expected to drive any external loads or ICs. EZ-PD™ PAG1S also has an internal configurable discharge path for the VBUS_IN rail, which is used to discharge the VBUS rail during negative voltage transitions.

The regulated supply VDDD, is either used to directly power some internal analog blocks or further regulated down to 1.8 V VCCD, which powers majority of the core. VDDD and VCCD is brought out on to pins to connect external capacitors for regulator stability, these are not meant to be used as power supplies.

1.1.5 VBUS_C, VBUS_CTRL

VBUS_C is used to monitor the voltage at the Type-C connector. VBUS_C has an internal configurable discharge path, which is used to discharge the VBUS_C rail during negative voltage transitions.

The load switch is between VBUS_IN and VBUS_C. EZ-PD™ PAG1S integrates a NFET gate driver to control this load switch. VBUS_CTRL is the output of this gate driver. To turn off the external NFET, the gate driver drives low. To turn on the external NFET, it drives the gate to VBUS_IN + 8 V. In addition, there is a clamp circuit to limit the gate to VBUS_IN + 8 V.

1.1.6 CSP, CSN

EZ-PD™ PAG1S integrates a LSCSA to monitor the load current. CSP is the positive input pin for the LSCSA and CSN is the negative input. LSCSA offers wide gain options ranging from 5 to 150. Suggested Rsense for LSCSA is 5 mΩ. LSCSA has an active offset cancellation mechanism to improve accuracy.

1.1.7 GPIO0, GPIO1, and GPIO3

EZ-PD™ PAG1S has six GPIOs, out of which three are dedicated GPIOs and the rest are multiplexed with other functionalities. During power-on and reset, the I/O pins (except GPIO1) are forced to the tristate so as not to crowbar any inputs and/or cause excess turn-on current. GPIO1 is driven to zero at power-up.

1.1.8 XRES

The XRES pin can be used to initiate a reset, this pin is internally pulled high and needs to be pulled low externally to trigger reset.

2 Application overview

2.1 USB Power Delivery power adapter

Figure 4 shows a power adapter application diagram implementing a primary side controlled synchronous flyback system. In this system, EZ-PD™ PAG1S engages the error amplifier to take the feedback from the secondary side and pass it on to the primary controller over an isolation barrier like an opto-isolator. The primary side controller can be any standard flyback controller. In this topology, EZ-PD™ PAG1S integrates three key features: secondary side sensing and regulation, SR, and charging port controller.

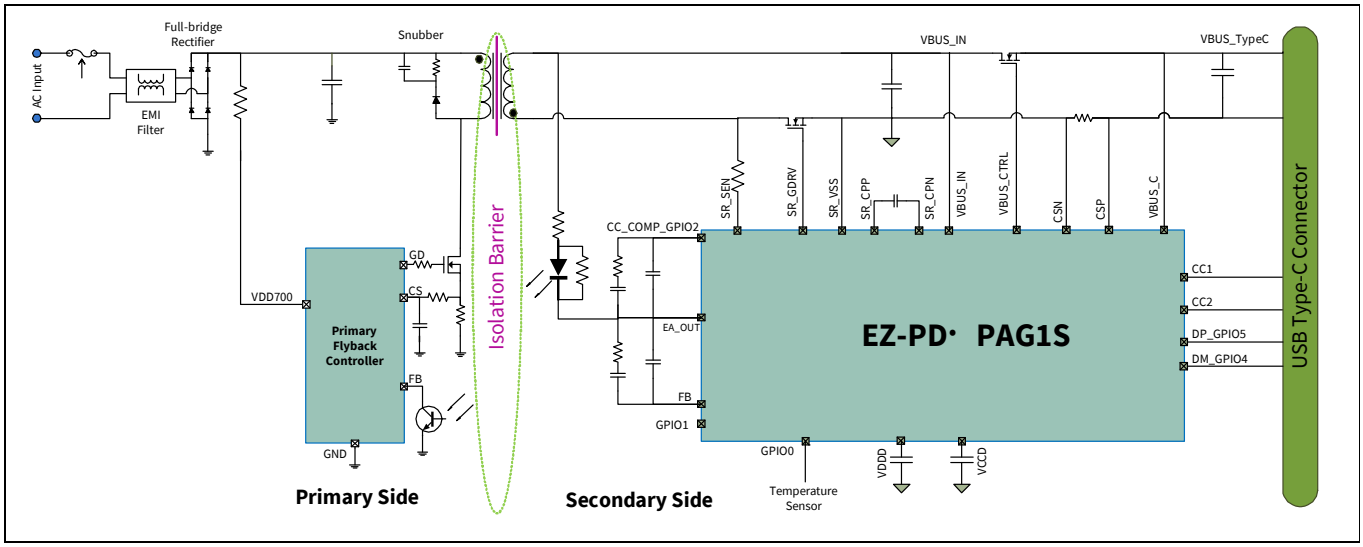


Figure 4 Power adapter with primary side control application diagram

3 Functional description

3.1 Start-up behavior

On power-up, the primary side flyback controller shall start controlling the primary switch using its internal primary peak current limited soft start mechanism and provide sufficient current to charge the secondary side output capacitor and the startup current required for EZ-PD™ PAG1S. The secondary output voltage is the input power supply source of EZ-PD™ PAG1S. Once this voltage at VBUS_IN crosses 3.3 V, EZ-PD™ PAG1S gets powered up. EZ-PD™ PAG1S firmware boot-up time is in the order of a few milliseconds. Once the boot-up is complete, EZ-PD™ PAG1S configures the error-amplifier to achieve 5 V secondary output. The output of the error-amplifier is passed on to the primary controller through an opto-coupler.

3.2 Fault protection

3.2.1 VBUS UVP and OVP

VBUS undervoltage and overvoltage faults are monitored using internal VBUS_IN/VBUS_C resistor dividers. The fault thresholds and response times are configurable in EZ-PD™ PAG1S. Configurability includes choosing between auto-restart or latch-off options for each fault.

3.2.2 VBUS OCP and SCP

VBUS overcurrent and short-circuit faults are monitored using internal current sense amplifiers. Same as OVP and UVP, the OCP and SCP fault thresholds and response times are configurable as well. Configurability includes choosing between auto-restart or latch-off options for each fault.

3.2.3 OTP

Overtemperature monitoring is done using an external thermistor and internal ADC. The thermistor can be connected to any free GPIO.

3.2.4 ESD protection

EZ-PD™ PAG1S offers ESD protection on all the pins. The ESD protection level is 2.2-kV HBM and 500-V CDM.

3.2.5 VBUS to CC short protection

EZ-PD™ PAG1S offers protection against accidental short from VBUS_C pin short to CC.

3.3 Power modes

EZ-PD™ PAG1S supports three power modes - Active, Sleep, and Deep Sleep. Transitions between these modes is handled by the device depending on the operating conditions.

4 Electrical specifications

4.1 Absolute maximum ratings

Table 3 Absolute maximum ratings[1]

Parameter	Description	Min	Typ	Max	Unit	Details/conditions
$V_{BUS\_IN\_MAX}$	Maximum input supply voltage	–	–	24	V	–
V_{DDD_MAX}	Maximum supply voltage	–	–	6		–
V_SR_DRAIN_MAX	Maximum voltage on SR_SEN pin	–	–	24		–
V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DDD} + 0.5		–
$V_{CC\_PIN\_ABS}$	Maximum voltage on CC1, CC2 voltage	–	–	24		–
I_{GPIO_ABS}	Current per GPIO	–	–	25	mA	–
ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
ESD_CDM	Electrostatic discharge charged device model	500	–	–		–
I_LU	Pin current for latch-up	–100	–	100	mA	–

Note

1. Usage of the absolute maximum conditions listed in **Table 3** may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150°C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.

4.2 Device-level specifications

Table 4 DC specifications

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
SID.PWR.1	V_{DDD_REG}	V_{DDD} output for 5.5 V ≤ V_{BUS_IN} ≤ 21.5 V	4.6	5.0	5.4	V	I_{LOAD} = 0-50 mA
SID.PWR.2	V_{DDD_MIN}	V_{DDD} output for 3.3 V ≤ V_{BUS_IN} ≤ 5.5 V	V_{BUS_IN} – 0.3	–	–		
SID.PWR.4	V_{BUS_IN}	Power supply input voltage	3.3	–	21.5		–
SID.PWR.6	V_{CCD}	Output voltage for core logic	–	1.8	–		–
SID.PWR.8	Cefc	Bypass capacitor for V_{CCD}	0.8	1	1.2	µF	X5R ceramic or better
SID.PWR.9	Cexc	Decoupling capacitor for V_{DDD}	1.8	–	2.2		
SID.PWR.10	Cexv	Decoupling capacitor for V_{BUS_IN}	–	1	–		Decoupling capacitor required near the IC pin.
SID.PWR.10A	Cexcpp	Capacitor between SR_CPP and SR_CPN pins	0.1	–	–		X5R ceramic or better
SID.PWR.15	I_{DD_A}	Active current from V_{BUS_IN} in Type-C attached state	–	25	–	mA	V_{BUS_IN} = 5 V, T_A = 25°C, CC1/CC2 in TX or RX
SID.PWR.16	$I_{DD\_S\_UA}$	Sleep current from V_{BUS_IN} in Type-C attached state	–	3.5	–		V_{BUS_IN} = 5 V, T_A = 25°C, Type-C attached
SID.PWR#16_A	$I_{\_DS\_UA}$	Deep Sleep current from V_{BUS_IN} (Type-C unattached)	–	0.75	–		V_{BUS_IN} = 5 V, T_A = 25°C, Type-C unattached, CPU OFF, UVOV block ON, WDT Wakeup ON.
SID.PWR.17	$V_{\_SR\_DRAIN}$	Voltage allowed on SR_SEN pin	–0.7	–	21.5	V	–

Table 5 AC specifications

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
SID.PWR.14	Tsleep	Wakeup from Sleep mode	–	0	–	µs	–
SID.PWR.14A	Tdeepsleep	Wakeup from Deep Sleep mode	–	35	–	µs	–

4.3 Functional block specifications

Table 6 ADC specifications

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.ADC.1	Resolution	ADC resolution	–	8	–	Bits	–
SID.ADC.2	INL	Integral nonlinearity	–2.5	–	2.5	LSB	Reference voltage = VREF_ADC1
SYS.ADC.3	INL		–1.5	–	1.5		Reference voltage = VREF_ADC2
SYS.ADC.4	DNL	Differential nonlinearity	–2.5	–	2.5		Reference voltage = VREF_ADC1
SYS.ADC.5	DNL		–1.5	–	1.5		Reference voltage = VREF_ADC2
SYS.ADC.6	Gain Error	Gain error	–1.5	–	1.5		–
SYS.ADC.7	VREF_ADC1	ADC reference voltage	V_{DDDmin}	–	V_{DDDmax}	V	Reference voltage generated from V_{DDD}
SYS.ADC.8	VREF_ADC2		1.96	2.0	2.04		Reference voltage generate from bandgap
AC specifications							
SID.ADC.9	Slew_Max	Rate of change of sampled voltage signal	–	–	3	V/ms	Guaranteed by design

Table 7 Error amplifier

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.DC.VR.1	V_R	VBUS voltage regulation accuracy	–	± 3	± 5	%	–
SID.DC.VR.2	Ika_off	Off-state EA_OUT current	–	2.2	10	µA	–
SID.DC.VR.3	Ika_on	Current through EA_OUT pin when in Sink mode for optocoupler application	–	–	5	mA	–
SID.DC.VR.4	DNL_ndac	Differential nonlinearity of NMOS DAC	–1	–	1	LSB	–
SID.DC.VR.5	INL_ndac	Integral nonlinearity of NMOS DAC	–1.5	–	1.5		–
SID.DC.VR.6	Gain_ error_ndac	Gain error of NMOS DAC	–8	–	8	%	–
SID.DC.VR.7	DNL_pdac	Differential nonlinearity of PMOS DAC	–0.5	–	0.5	LSB	–
SID.DC.VR.8	INL_pdac	Integral nonlinearity of PMOS DAC	–1	–	1		–
SID.DC.VR.9	Gain_ error_pdac	Gain error of PMOS DAC	–8	–	8	%	–

Table 8 LSCSA, SCP

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.LSCSA.1	Cin_inp	CSP input capacitance	–	–	10	pF	–
SID.LSCSA.2	Csa_Acc1	CSA accuracy with 5 mV < Vsense < 10 mV	–15	–	15	%	–
SID.LSCSA.3	Csa_Acc2	CSA accuracy with 10 mV < Vsense < 15 mV	–10	–	10		–
SID.LSCSA.4	Csa_Acc3	CSA accuracy with 15 mV < Vsense	–5	–	5		–
SID.LSCSA.5	SCP_6A	Short circuit trip point with threshold set to 6 A	5.4	6	6.6	A	Rsense = 5 mΩ
SID.LSCSA.6	SCP_10A	Short circuit trip point with threshold set to 10 A	9	10	11		
SID.LSCSA.8	Av	CSA gain values supported: 5,10, 20, 35, 50, 75, 125, 150	5	–	150		–

Table 8 LSCSA, SCP *(continued)*

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
AC specifications							
SID.LSCSA.AC.1	Tocp_gate	Delay from OCP threshold trip to external NFET gate turn off	–	4	20	µs	–
SID.LSCSA.AC.2	Tscp_gate	Delay from SCP threshold trip to external NFET gate turn off	–	3.1	–		1 nF NFET gate capacitance
SID.LSCSA.AC.3	Tscp_gate_1	Delay from SCP threshold trip to external NFET power gate turn off	–	7.5	–		3 nF NFET gate capacitance

Table 9 VBUS UV, OV

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.UVOV.1	VTHOV1	Over-Voltage threshold Accuracy, 4 V to 11 V	–3	–	3	%	–
SID.UVOV.2	VTHOV2	Over-Voltage threshold Accuracy, 11 V to 21.5 V	–3.2	–	3.2		–
SID.UVOV.3	VTHUV1	Under-Voltage threshold Accuracy, 3 V to 3.3 V	–4	–	4		–
SID.UVOV.4	VTHUV2	Under-Voltage threshold Accuracy, 3.3 V to 4.0 V	–3.5	–	3.5		–
SID.UVOV.5	VTHUV3	Under-Voltage threshold Accuracy, 4.0 V to 11 V	–3	–	3		–
SID.UVOV.6	VTHUV4	Under-Voltage threshold Accuracy, 11 V to 21.5 V	–2.9	–	2.9		–
AC specifications							
SID.UVOV.AC.1	Tov_gate	Delay from OV threshold trip to external NFET Power Gate Turn off	–	–	50	µs	–

Table 10 PD transceiver

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.PD.1	Rp_std	Downstream facing port (DFP) CC termination for default USB power	64	80	96	µA	–
SID.PD.2	Rp_1.5A	DFP CC termination for 1.5 A USB power	166	180	194		–
SID.PD.3	Rp_3.0A	DFP CC termination for 3.0 A USB power	304	330	356		–
SID.PD.4	Vgndoffset	Ground offset tolerated by BMC receiver	–500	–	500	mV	Relative to remote BMC transmitter

Table 11 VBUS discharge

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.VBUS.DISC.1	R1	20 V NMOS ON resistance for discharge strength = 1	500	–	2000	Ω	Measured at 0.5 V
SID.VBUS.DISC.2	R2	20 V NMOS ON resistance for discharge strength = 2	250	–	1000		
SID.VBUS.DISC.3	R4	20 V NMOS ON resistance for discharge strength = 4	125	–	500		
SID.VBUS.DISC.4	R8	20 V NMOS ON resistance for discharge strength = 8	62.5	–	250		
SID.VBUS.DISC.5	R16	20 V NMOS ON resistance for discharge strength = 16	31.25	–	125		
SID.VBUS.DISC.6	Vbus_stop_error	Error percentage of final VBUS value	–	–	10	%	When VBUS is discharged to 5 V

Table 12 VBUS NFET gate driver

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.GD.1	GD_VGS	Gate to Source overdrive during NFET ON condition	4.5	5.75	10	V	Vbus_in = 21.5 V
SID.GD.2	GD_Rpd	Resistance when pull-down is enabled to turn off external NFET	–	0.57	2	kΩ	–
AC specifications							
AC.GD.1	Ton	V_{BUS_ctrl} Low to High (1 V to V_{BUS} + 1 V) with 3 nF external capacitance	2	5	10	ms	V_{BUS_IN} = 5 V
AC.GD.2	Toff	V_{BUS_ctrl} High to Low (90% to 10%) with 3 nF external capacitance	–	7	–	µs	V_{BUS_IN} = 21.5 V

Table 13 High-voltage regulator

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.VREG.1	VOLTAGE_ DETECT	VBUS_IN voltage detect threshold	1.7	2.1	2.4	V	–
SID.VREG.2	Tstart	Total start-up time for the regulator supply outputs	–	50	200	µs	From VBUS reaching Voltage_detect level to 95% of final value

Table 14 SR sense and driver

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SR.1	VCPP1	Voltage doubler output for 3.3 V ≤ VBUS_IN ≤ 5.5 V	5	–	–	V	–
SR.2	VCPP2	Voltage doubler output for 5.5 V ≤ VBUS_IN ≤ 21.5 V	9	–	11		–
SR.3	TR_SR	Rise time (20% to 80%) of SR gate driver output with CL = 6 nF, VBUS_IN = 3.3 V, including doubler rise time (with and without double bypass mode)	–	–	150	ns	–
SR.4	TF_SR	Fall time (80% to 20%) of SR gate driver output with CL = 6 nF, VBUS_IN = 3.3 V, including doubler rise time (with and without double bypass mode)	–	–	100		–
SR.5	IIK_SR_VSS	Input leakage current on SR_VSS	–1	–	1	µA	–
SR.6	VTRIP_ NSN_100	Negative sense trip voltage to turn-ON secondary switch	–140	–90	–60	mV	–
SR.7	VTRIP_ZCD	Negative sense trip voltage to turn-OFF secondary switch	–8	–5	–3		–
SR.8	TD_ON	Turn on propagation delay from SR_SEN at –100mV to SR_GDRV reaching 1V	–	25	50	ns	–
SR.9	TD_OFF	Turn off propagation delay from SR_SEN at –5mV to SR_GDRV reaching 1V	–	100	200		–
SR.10	IO_SRC_SNK	Output peak current (Source and Sink)	–	1	–	A	Typical with 3 nF gate cap (Guaranteed by design)

4.4 I/O specifications

Table 15 I/O specifications

Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
DC specifications							
SID.GIO.1	I_LU	Latch-up current limits	–140	–	140	mA	–
SID.GIO.2	RPU	Pull-up resistor value	3.5	5.6	8.5	kΩ	–
SID.GIO.3	RPD	Pull-down resistor value	3.5	5.6	8.5		–
SID.GIO.4	IIL	Input leakage current	–		2	nA	–
SID.GIO.5	CPIN_A	Max pin capacitance	–	7.8	22	pF	Capacitance on DP/DM lines
SID.GIO.6	CPIN		–	3	7		Capacitance on all GPIOs, except DP/DM lines
SID.GIO.7	Voh_3V	Output voltage high level	V_{DDD} – 0.6	–	–	V	Ioh = –4 mA
SID.GIO.8	Vol_3V	Output voltage low level	–	–	0.6		Iol = 10 mA
SID.GIO.9	Vih_CMOS	Input voltage high threshold	0.7 × V_{DDD}	–	–		–
SID.GIO.10	Vil_CMOS	Input voltage low threshold	–	–	0.3 × V_{DDD}		–
SID.GIO.11	Vih_TTL	LVTTL input	2	–			–
SID.GIO.12	Vil_TTL		–	–	0.8		–
SID.GIO.13	Vhysttl	Input hysteresis LVTTL	100	–	–	mV	–
SID.GIO.14	Vhyscmos	Input hysteresis CMOS	0.05 × V_{DDD}	–	–		–
SID.GIO.15	IDIODE	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	–
SID.GIO.16	TriseF	Rise time in fast strong mode	2	–	12	ns	Cload = 25 pF
SID.GIO.17	TfallF	Fall time in fast strong mode	2	–	12		
SID.GIO.18	TriseS	Rise time in slow strong mode	10	–	60		
SID.GIO.19	TfallS	Fall time in slow strong mode	10	–	60		
SID.GIO.20	FGPIO_OUT1	GPIO Fout; 3 V ≤ V_{DDD} ≤ 5.5V; Fast strong mode.	–	–	16	MHz	
SID.GIO.21	FGPIO_OUT2	GPIO Fout; 3V ≤ V_{DDD} ≤ 5.5 V; Slow strong mode.	7	–	–		
SID.GIO.22	FGPIO_IN	GPIO input operating frequency; 3 V ≤ V_{DDD} ≤ 5.5 V	16	–	–		–

4.5 System resources specifications

Table 16 Power-on reset (POR) specifications

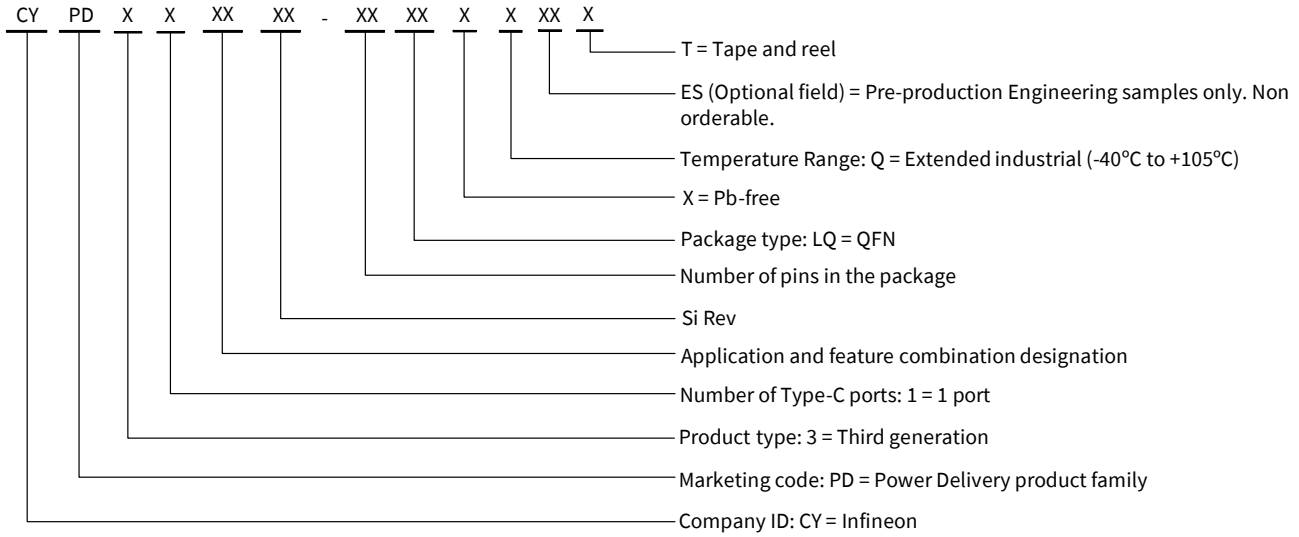
Spec ID	Parameter	Description	Min	Typ	Max	Unit	Details/conditions
SID.POR.1	VRISEIPOR	POR rising trip voltage	0.8	–	1.5	V	–
SID.POR.2	VFALLIPOR	POR falling trip voltage	0.7	–	1.4		–
SID.POR.3	VFALLPPOR	Brown-out-detect (BOD) trip voltage active/ sleep modes	1.48	–	1.62		–
SID.CLK#6	SR_POWER	Power supply slew rate	0.40	–	67	V/ms	On power-up and power-down

5 Ordering information

Table 17 EZ-PD™ PAG1S ordering information

MPN	Application	Package type	Si ID	Si Rev
CYPD3184A1-24LQXQ	USB Power Delivery adapter with primary side control	24-pin QFN	2B00	A1
CYPD3184A1-24LQXQT				

5.1 Ordering code definitions



6 Packaging

Table 18 Package characteristics

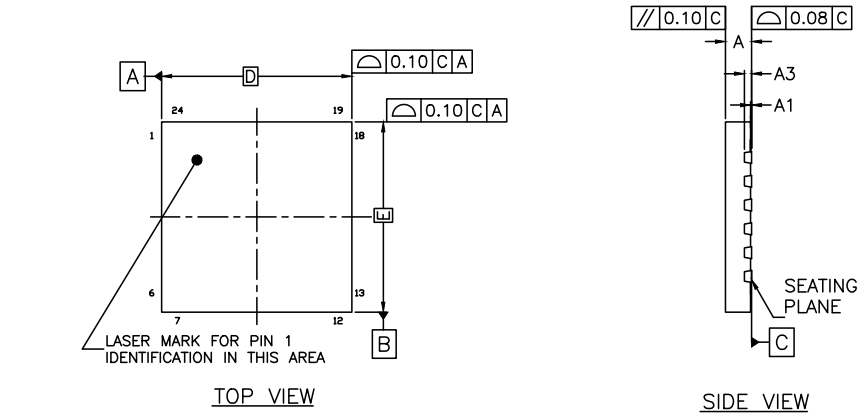
Parameter	Description	Conditions	Min	Typ	Max	Unit
T_A	Operating ambient temperature	Extended industrial	–40	25	105	°C
T_J	Operating junction temperature		–40	25	120	
T_{JA}	Package θ_{JA}	–	–	–	19.98	°C/W
T_{JC}	Package θ_{JC}		–	–	4.78	

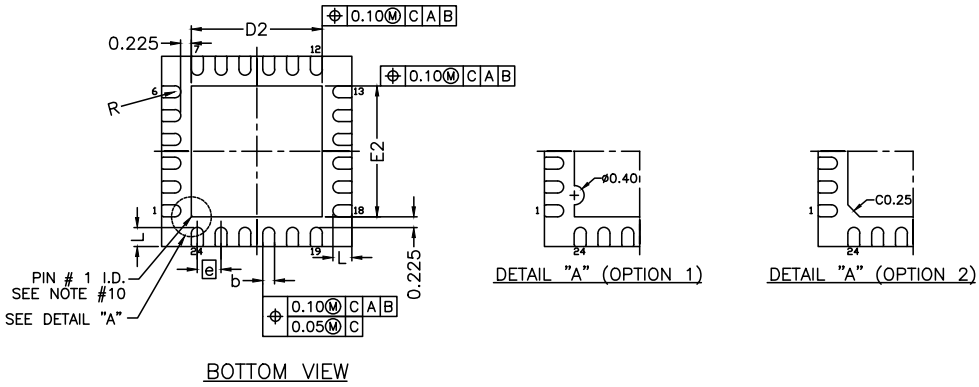
Table 19 Solder reflow peak temperature

Package	Maximum peak temperature	Maximum time within 5°C of peak temperature
24-pin QFN	260°C	30 seconds

Table 20 Package moisture sensitivity level (MSL), IPC/JEDEC J-STD-2

Package	MSL
24-pin QFN	MSL 3





SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	—	—	0.60
A1	0.00	—	0.05
A3 (Option 1)	0.152 REF		
A3 (Option 2)	0.127 REF		
b	0.18	0.25	0.30
D	4.00 BSC		
D2	2.65	2.75	2.85
E	4.00 BSC		
E2	2.65	2.75	2.85
L	0.30	0.40	0.50
e	0.50 BSC		
R	0.09	—	—

NOTES

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIE THICKNESS ALLOWABLE IS 0.305 mm MAXIMUM(.012 INCHES MAXIMUM)
3. DIMENSIONING & TOLERANCES CONFORM TO ASME Y14.5M. -1994.
4. THE PIN #1 IDENTIFIER MUST BE PLACED ON THE TOP SURFACE OF THE PACKAGE BY USING INDENTATION MARK OR OTHER FEATURE OF PACKAGE BODY.
5. EXACT SHAPE AND SIZE OF THIS FEATURE IS OPTIONAL.
6. PACKAGE WARPAGE MAX 0.08 mm.
7. APPLIED FOR EXPOSED PAD AND TERMINALS. EXCLUDE EMBEDDING PART OF EXPOSED PAD FROM MEASURING.
8. APPLIED ONLY TO TERMINALS.
9. JEDEC SPECIFICATION NO. REF: N.A.
10. INDEX FEATURE CAN EITHER BE AN OPTION 1 : "MOUSE BITE" OR OPTION 2 : CHAMFER.

002-16934 *E

Figure 5 24-pin QFN ((4.0 × 4.0 × 0.6 mm), 2.75 × 2.75 mm E-Pad (Sawn)) package outline, 002-16934

7 Acronyms

Table 21 Acronyms used in this document

Acronym	Description
ADC	analog-to-digital converter
API	application programming interface
Arm®	advanced RISC machine, a CPU architecture
CC	constant current
CC	configuration channel
CV	constant voltage
BOD	Brown out Detect
BMC	biphase mark code
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
CrCM	critical conduction mode
CS	current sense
DCM	discontinuous conduction mode
DFP	downstream facing port
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DRP	dual role port
EEPROM	electrically erasable programmable read-only memory
EMCA	a USB cable that includes an IC that reports cable characteristics (e.g., current rating) to the Type-C ports
EMI	electromagnetic interference
ESD	electrostatic discharge
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output
IC	integrated circuit
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
I/O	input/output, see also GPIO
LSCSA	low-side current sense amplifier
LVD	low-voltage detect
LVTTL	low-voltage transistor-transistor logic
MCU	microcontroller unit
NC	no connect
NMI	nonmaskable interrupt
NMOS	N-type metal-oxide-semiconductor

Table 21 Acronyms used in this document *(continued)*

Acronym	Description
NVIC	nested vectored interrupt controller
opamp	operational amplifier
OCP	overcurrent protection
OVP	overvoltage protection
OTP	over-temperature protection
PCB	printed circuit board
PD	power delivery
PGA	programmable gain amplifier
PHY	physical layer
PMOS	P-type metal-oxide-semiconductor
POR	power-on reset
PPS	programmable power supply
PRES	precise power-on reset
PSoC™	programmable system-on-chip
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RX	receive
SAR	successive approximation register
SCL	I^2C serial clock
SCP	short circuit protection
SDA	I^2C serial data
S/H	sample and hold
SPI	Serial Peripheral Interface, a communications protocol
SR	synchronous rectifier
SRAM	static random access memory
SWD	serial wire debug, a test protocol
TX	transmit
Type-C	a new standard with a slimmer USB connector and a reversible cable, capable of sourcing up to 100 W of power
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
USB	Universal Serial Bus
USBIO	USB input/output, CCG5 pins used to connect to a USB port
UVP	undervoltage protection
WDT	watchdog timer
USBIO	USB input/output, CCG5 pins used to connect to a USB port
XRES	external reset I/O pin
ZCD	zero crossing detect

8 Document conventions

8.1 Units of measure

Table 22 Units of measure

Symbol	Unit of measure
°C	degrees Celsius
Hz	hertz
KB	1024 bytes
kHz	kilohertz
kΩ	kilo ohm
Mbps	megabits per second
MHz	megahertz
MΩ	mega-ohm
Msps	megasamples per second
µA	microampere
µF	microfarad
µs	microsecond
µV	microvolt
µW	microwatt
mA	milliampere
ms	millisecond
mV	millivolt
nA	nanoampere
ns	nanosecond
Ω	ohm
pF	picofarad
ppm	parts per million
ps	picosecond
s	second
sps	samples per second
V	volt

Revision history

Document version	Date of release	Description of changes
*B	2019-08-22	Changed document status from Preliminary to Final.
*C	2022-05-18	Updated **Ordering information**: Updated part numbers. Updated **Packaging**: spec 002-16934 – Changed revision from *B to *E. Migrated to Infineon template.
*D	2022-06-16	Updated **Electrical specifications**: Updated **Device-level specifications**: Updated **Table 4**: Changed maximum value of Cexc parameter from 4.7 µF to 2.2 µF. Updated **System resources specifications**: Updated **Table 16**: Added SR_POWER parameter and its corresponding details. Completing Sunset Review.

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